

METHOD OF FORMING REFRACTORY METAL CONTACT IN AN OPENING, AND RESULTING STRUCTURE

ABSTRACT OF THE DISCLOSURE

5 A method of ensuring against deterioration of an underlying silicide layer over which a refractory material layer is deposited by physical vapor deposition (PVD) or chemical vapor deposition (CVD) is realized by first providing a continuous polysilicon layer prior to the refractory material deposition. The continuous polysilicon layer, preferably no thicker than 50 Å, serves a sacrificial purpose and prevents interaction between any fluorine that is released during the refractory material deposition step from interacting with the underlying silicide.

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